conductive interconnections provided in a plurality of layers separated by said interlayer insulating films;

conductive dummy interconnections provided in the plurality of layers so that each conductive dummy interconnection is formed in a layer of said plurality of layers with at least one conductive interconnection; and

a conductive dummy plug selectively buried in said interlayer insulating films to connect said dummy interconnections between said two or more layers and connected together with said dummy interconnections to a stable potential line which is included in said interconnections and which holds a constant potential with respect to a potential carried on a lower-potential power-supply line or a higher-potential power-supply line.

7. (Amended) The semiconductor device according to claim 1, wherein said dummy interconnections are provided to sandwich an interconnection part included in said interconnections in at least one layer of said plurality of layers.

IN THE ABSTRACT

Page 54, lines 2-7, please amend the abstract to read as follows:

A semiconductor device which reduces a noise superimposed upon a signal carried on an interconnection or cross-talk. Dummy interconnections are formed in the same layers respectively as interconnections formed in a plurality of layers. The dummy interconnections are connected through dummy plugs. At least the dummy interconnections and the dummy plugs are fixed at a ground potential and barrier layers are formed between the same layers and at least one of the conductive interconnections, the conductive dummy interconnections and the conductive dummy plug.